

SNCE N-Channel Enhancement Mode Power MOSFET

Description

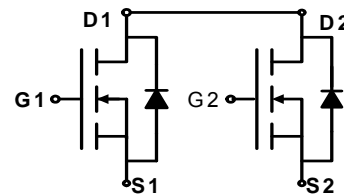
The ZL8810E uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

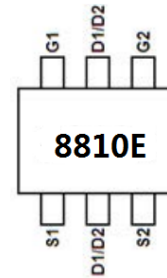
- $V_{DS} = 20V, I_D = 6.5A$
 $R_{DS(ON)} < 23m\Omega @ V_{GS}=2.5V$
 $R_{DS(ON)} < 18m\Omega @ V_{GS}=4.5V$
- High power and current handling capability
- Lead free product is acquired
- Surface mount package
- ESD Protected

Application

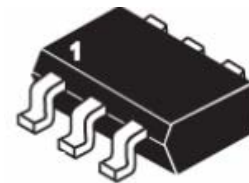
- Battery protection
- Load switch
- Power management



Schematic diagram



Marking and pin assignment



SOT23-6L top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
8810E	ZL8810E	SOT23-6L	Ø330mm	12mm	3000 units

Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 10	V
Drain Current-Continuous	I_D	7	A
Drain Current-Pulsed ^(Note 1)	I_{DM}	25	A
Maximum Power Dissipation	P_D	1.5	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ\text{C}$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient ^(Note 2)	$R_{\theta JA}$	83	$^\circ\text{C/W}$
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Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						

